

General Description

The AOD4128 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate resistance.

This device is ideally suited for use as a low side switch in CPU core power conversion. The device can also be used in PWM, load switching and general purpose applications.

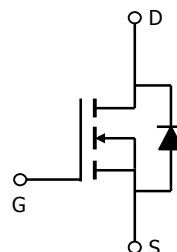
Features

$$V_{DS} (V) = 25V$$

$$I_D = 60 A \quad (V_{GS} = 10V)$$

$$R_{DS(ON)} < 4 m\Omega \quad (V_{GS} = 10V)$$

$$R_{DS(ON)} < 7 m\Omega \quad (V_{GS} = 4.5V)$$



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	I_D	$T_C=25^\circ C$	A
		$T_C=100^\circ C$	
Pulsed Drain Current ^C	I_{DM}	165	
Avalanche Current ^C	I_{AR}	45	
Repetitive avalanche energy $L=0.3mH$ ^C	E_{AR}	304	mJ
Power Dissipation ^B	P_D	$T_C=25^\circ C$	W
		$T_C=100^\circ C$	
Power Dissipation ^A	P_{DSM}	$T_A=25^\circ C$	W
		$T_A=70^\circ C$	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 175	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	18	25	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady State	50	60
Maximum Junction-to-Case ^B	$R_{\theta JC}$	1	2	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	25			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =25V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.3	1.6	2.5	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	165			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A		3.4	4	mΩ
		T _J =125°C		5.0	6	
		V _{GS} =4.5V, I _D =20A		5.8	7	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		55		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.7	1	V
I _S	Maximum Body-Diode Continuous Current ^G				60	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =12.5V, f=1MHz		3578	4300	pF
C _{oss}	Output Capacitance			731	950	pF
C _{rss}	Reverse Transfer Capacitance			438	615	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		2.5	4	Ω
SWITCHING PARAMETERS						
Q _{g(10V)}	Total Gate Charge	V _{GS} =10V, V _{DS} =12.5V, I _D =20A		61.8	80	nC
Q _{g(4.5V)}	Total Gate Charge			29.8	39	nC
Q _{gs}	Gate Source Charge			8.5		nC
Q _{gd}	Gate Drain Charge			12.9		nC
t _{D(on)}	Turn-On DelayTime			11.6		ns
t _r	Turn-On Rise Time	V _{GS} =10V, V _{DS} =12.5V, R _L =0.63Ω, R _{GEN} =3Ω		17.7		ns
t _{D(off)}	Turn-Off DelayTime			45		ns
t _f	Turn-Off Fall Time			20		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, di/dt=100A/μs		39	48	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, di/dt=100A/μs		32		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allow s it.

B: The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C.

D: The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C.

G: The maximum current rating is limited by bond-wires.

H: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

*This device is guaranteed green after data code 8X11 (Sep 1ST 2008).

Re1: Sep. 2008

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

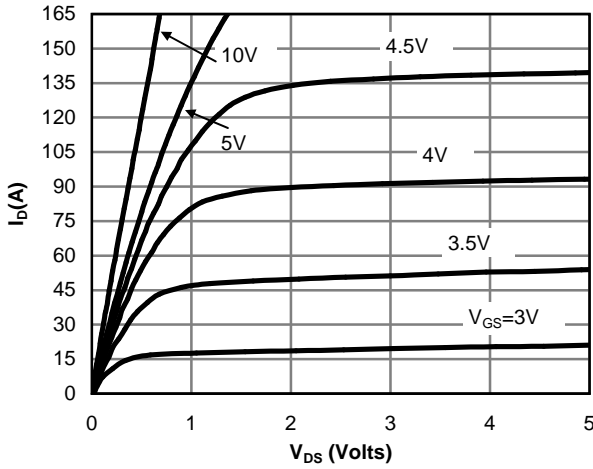


Figure 1: On-Region Characteristics

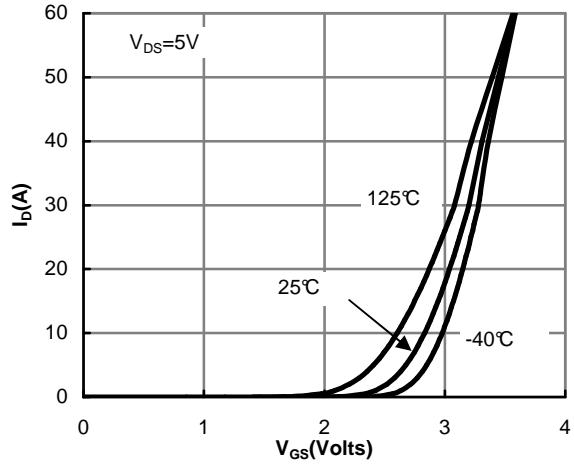


Figure 2: Transfer Characteristics

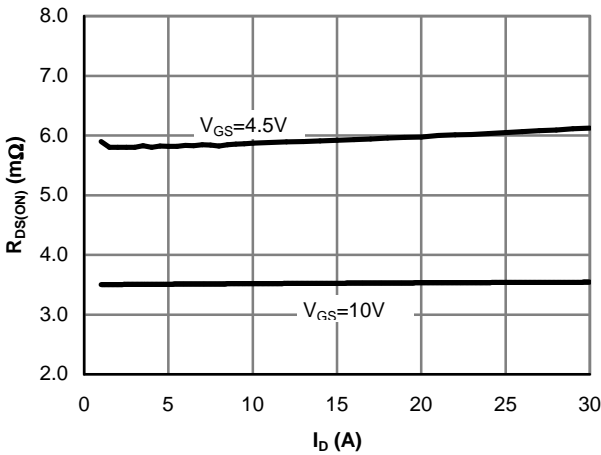


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

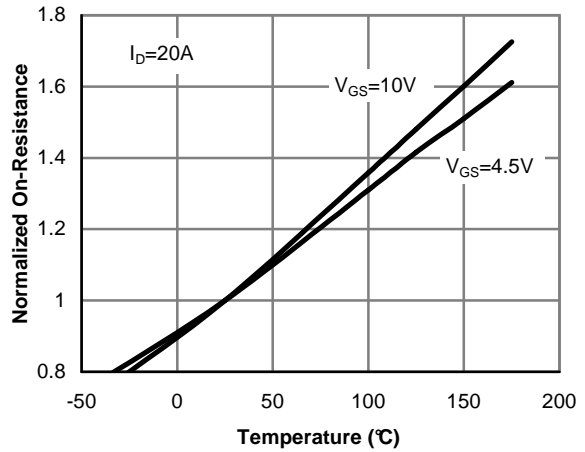


Figure 4: On-Resistance vs. Junction Temperature

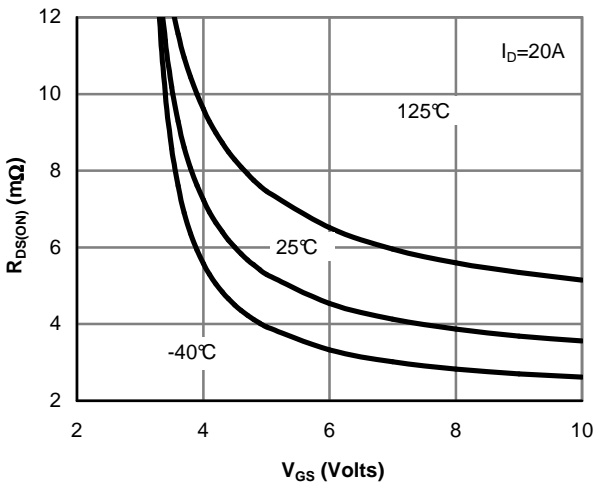


Figure 5: On-Resistance vs. Gate-Source Voltage

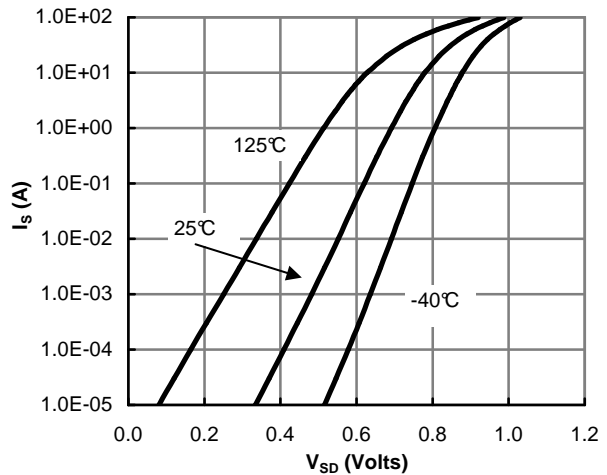


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

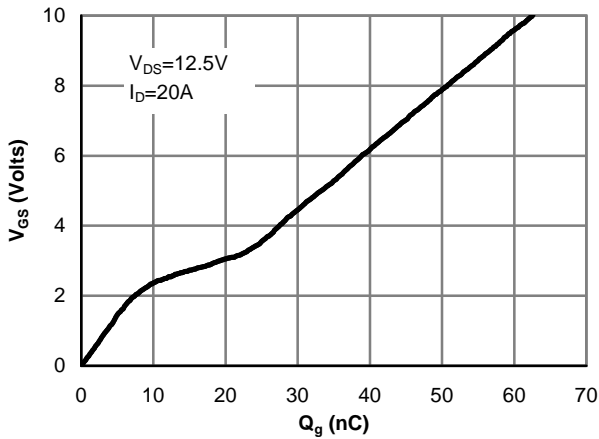


Figure 7: Gate-Charge Characteristics

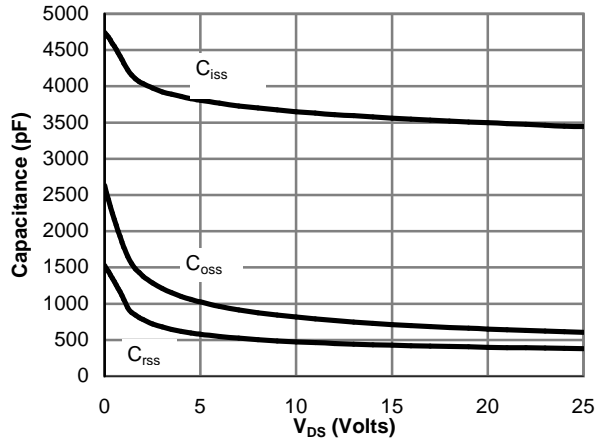


Figure 8: Capacitance Characteristics

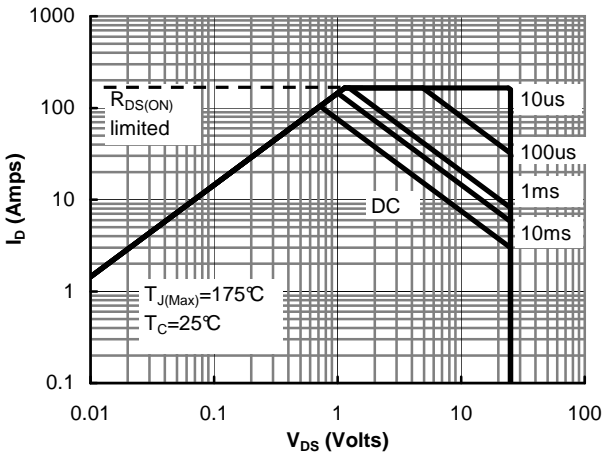


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

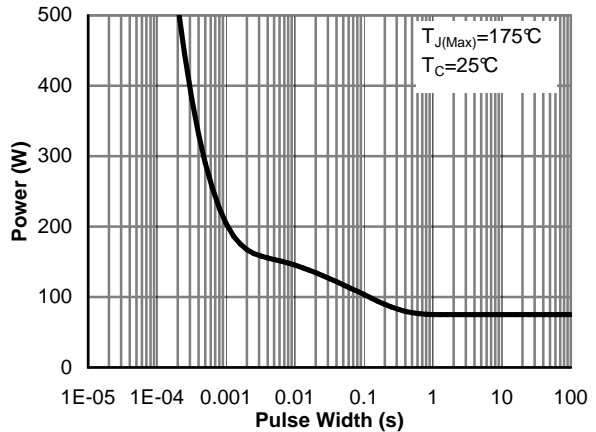


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

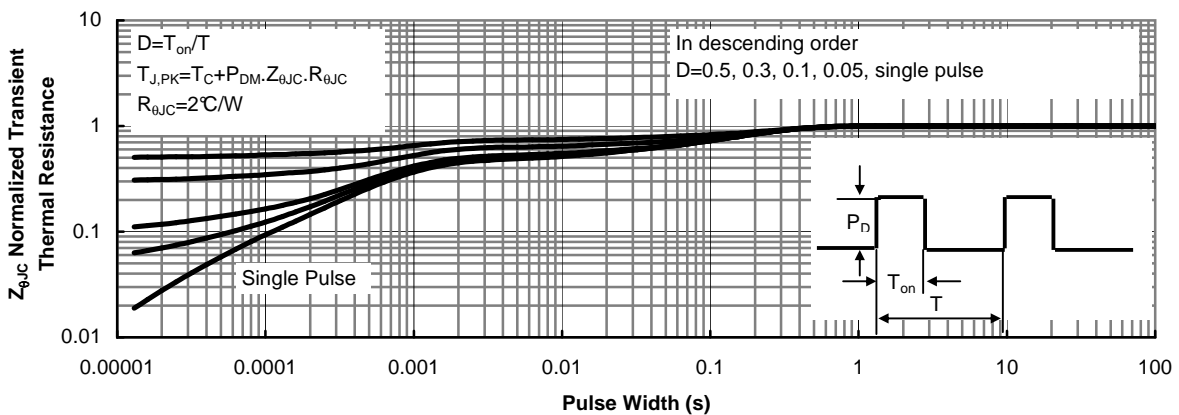


Figure 16: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

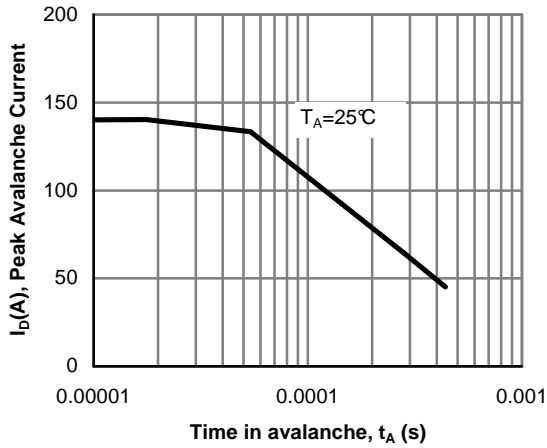


Figure 12: Single Pulse Avalanche capability

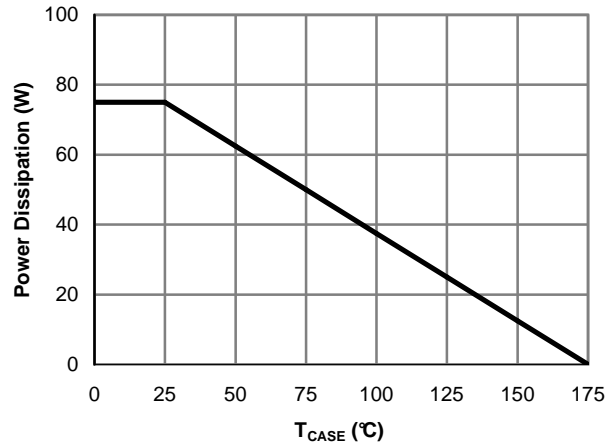


Figure 13: Power De-rating (Note B)

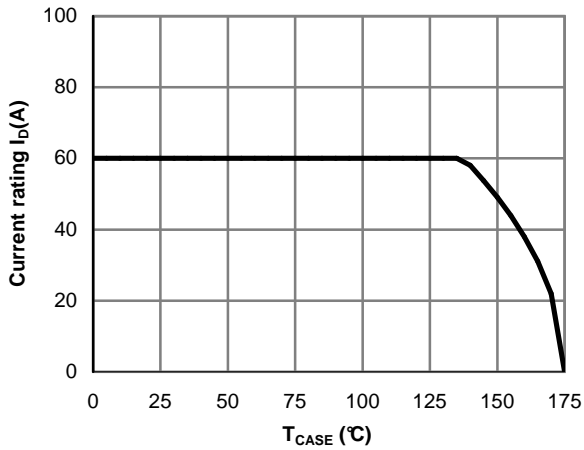


Figure 14: Current De-rating (Note B)

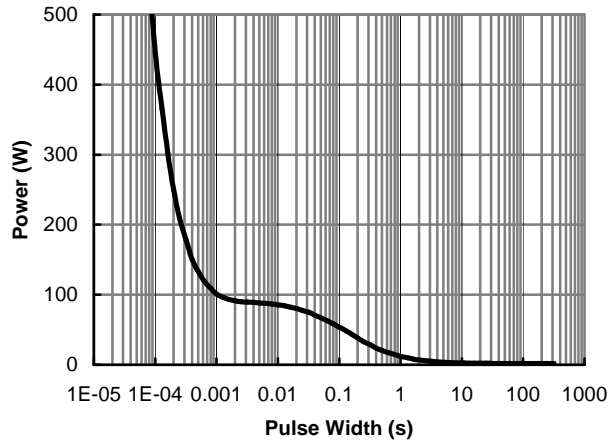


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

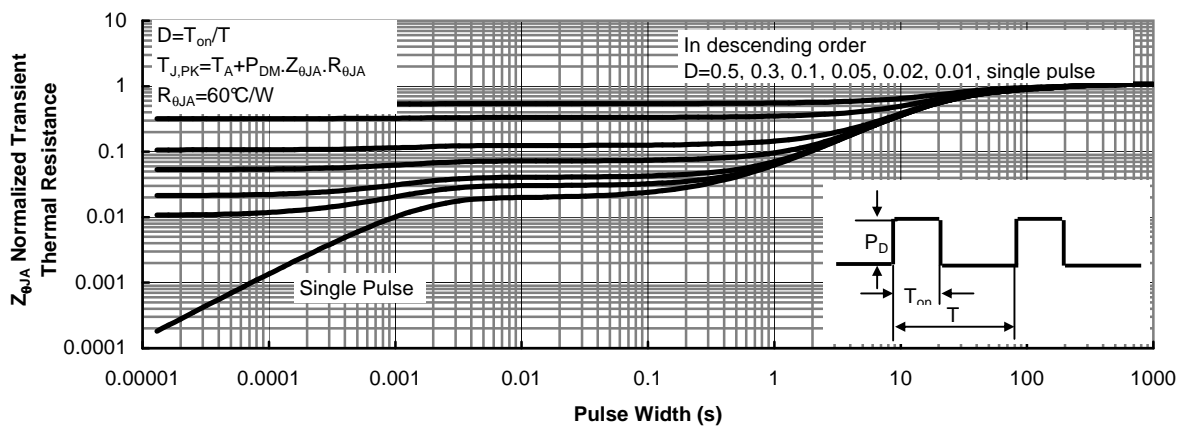
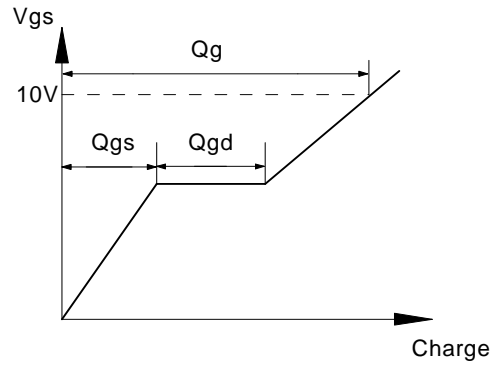
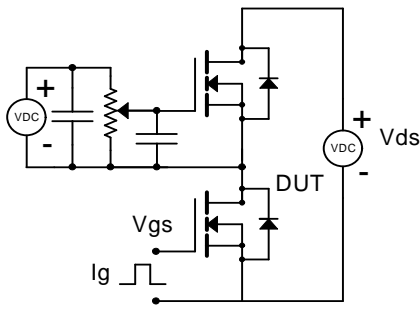
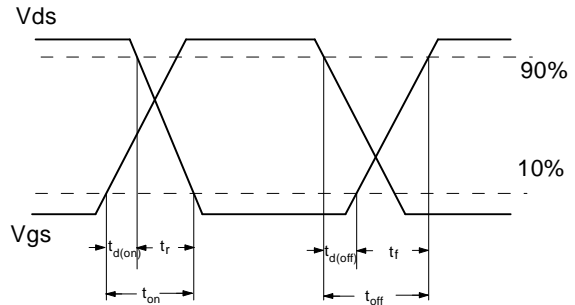
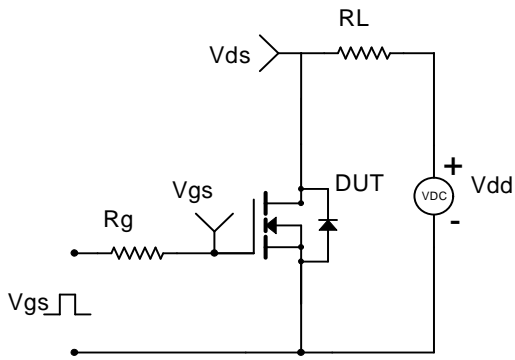


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

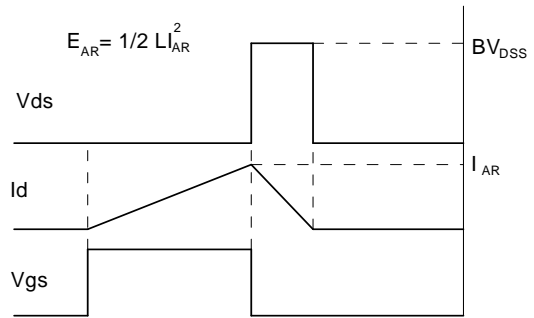
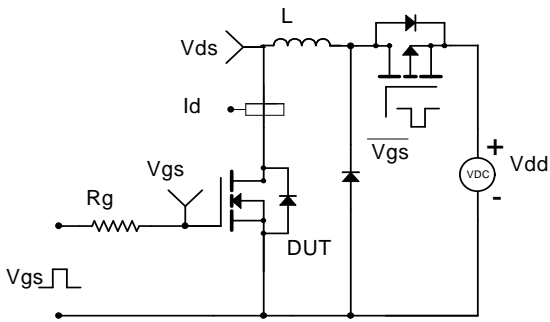
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

